

15A, 55V, 0.090 Ohm, N-Channel UltraFET Power MOSFETs



These N-Channel power MOSFETs are manufactured using the innovative UltraFET® process. This advanced process technology

achieves the lowest possible on-resistance per silicon area, resulting in outstanding performance. This device is capable of withstanding high energy in the avalanche mode and the diode exhibits very low reverse recovery time and stored charge. It was designed for use in applications where power efficiency is important, such as switching regulators, switching converters, motor drivers, relay drivers, low-voltage bus switches, and power management in portable and battery-operated products.

Formerly developmental type TA75307.

Ordering Information

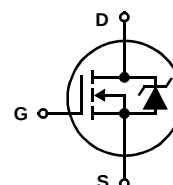
PART NUMBER	PACKAGE	BRAND
HUF75307P3	TO-220AB	75307P
HUF75307D3	TO-251AA	75307D
HUF75307D3S	TO-252AA	75307D

NOTE: When ordering, use the entire part number. Add the suffix T to obtain the TO-252AA variant in tape and reel, e.g., HUF75307D3ST.

Features

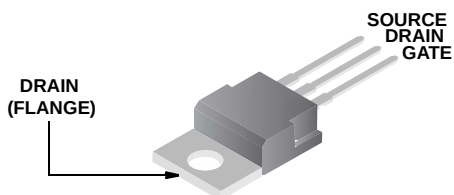
- 15A, 55V
- Simulation Models
 - Temperature Compensated PSPICE® and SABER™ Models
 - SPICE and SABER Thermal Impedance Models Available on the WEB at: www.fairchildsemi.com
- Peak Current vs Pulse Width Curve
- UIS Rating Curve
- Related Literature
 - TB334, "Guidelines for Soldering Surface Mount Components to PC Boards"

Symbol

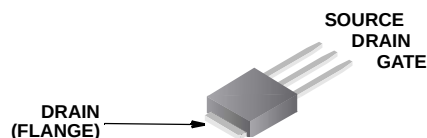


Packaging

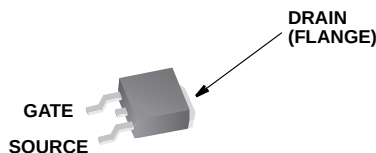
JEDEC TO-220AB



JEDEC TO-251AA



JEDEC TO-252AA



Product reliability information can be found at <http://www.fairchildsemi.com/products/discrete/reliability/index.html>

For severe environments, see our Automotive HUFA series.

All Fairchild semiconductor products are manufactured, assembled and tested under ISO9000 and QS9000 quality systems certification.

HUF75307P3, HUF75307D3, HUF75307D3S

Absolute Maximum Ratings $T_C = 25^{\circ}\text{C}$, Unless Otherwise Specified

			UNITS
Drain to Source Voltage (Note 1)	V_{DSS}	55	V
Drain to Gate Voltage ($R_{GS} = 20\text{k}\Omega$) (Note 1)	V_{DGR}	55	V
Gate to Source Voltage	V_{GS}	± 20	V
Drain Current			
Continuous (Figure 2)	I_D	15	A
Pulsed Drain Current	I_{DM}	Figure 4	
Pulsed Avalanche Rating	E_{AS}	Figures 6, 14, 15	
Power Dissipation	P_D	45	W
Derate Above 25°C		0.3	$\text{W}/^{\circ}\text{C}$
Operating and Storage Temperature	T_J, T_{STG}	-55 to 175	$^{\circ}\text{C}$
Maximum Temperature for Soldering			
Leads at 0.063in (1.6mm) from Case for 10s.	T_L	300	$^{\circ}\text{C}$
Package Body for 10s, See Techbrief 334	T_{pkg}	260	$^{\circ}\text{C}$

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. $T_J = 25^{\circ}\text{C}$ to 150°C .

Electrical Specifications $T_C = 25^{\circ}\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS	
OFF STATE SPECIFICATIONS							
Drain to Source Breakdown Voltage	BV _{DSS}	I _D = 250μA, V _{GS} = 0V (Figure 11)	55	-	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 50V, V _{GS} = 0V	-	-	1	μA	
		V _{DS} = 45V, V _{GS} = 0V, T _C = 150 ⁰ C	-	-	250	μA	
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±20V	-	-	±100	nA	
ON STATE SPECIFICATIONS							
Gate to Source Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250μA (Figure 10)	2	-	4	V	
Drain to Source On Resistance	r _{DS(ON)}	I _D = 15A, V _{GS} = 10V (Figure 9)	-	0.075	0.090	Ω	
THERMAL SPECIFICATIONS							
Thermal Resistance Junction to Case	R _{θJC}	(Figure 3)	-	-	3.3	⁰ C/W	
Thermal Resistance Junction to Ambient	R _{θJA}	TO-220AB	-	-	62	⁰ C/W	
		TO-251AA, TO-252AA	-	-	100	⁰ C/W	
SWITCHING SPECIFICATIONS (V _{GS} = 10V)							
Turn-On Time	t _{ON}	V _{DD} = 30V, I _D ≅ 15A, R _L = 2.0Ω, V _{GS} = 10V, R _{GS} = 100Ω	-	-	60	ns	
Turn-On Delay Time	t _{d(ON)}		-	7	-	ns	
Rise Time	t _r		-	40	-	ns	
Turn-Off Delay Time	t _{d(OFF)}		-	35	-	ns	
Fall Time	t _f		-	45	-	ns	
Turn-Off Time	t _{OFF}		-	-	100	ns	
GATE CHARGE SPECIFICATIONS							
Total Gate Charge	Q _{g(TOT)}	V _{GS} = 0V to 20V	V _{DD} = 30V, I _D ≅ 15A, R _L = 2.0Ω I _{g(REF)} = 1.0mA (Figure13)	-	16	20	nC
Gate Charge at 10V	Q _{g(10)}	V _{GS} = 0V to 10V		-	9	11	nC
Threshold Gate Charge	Q _{g(TH)}	V _{GS} = 0V to 2V		-	0.6	0.8	nC
Gate to Source Gate Charge	Q _{gs}			-	1.2	-	nC
Reverse Transfer Capacitance	Q _{gd}			-	4	-	nC

HUF75307P3, HUF75307D3, HUF75307D3S

Electrical Specifications $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
CAPACITANCE SPECIFICATIONS						
Input Capacitance	C_{ISS}	$V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$ (Figure 12)	-	250	-	pF
Output Capacitance	C_{OSS}		-	100	-	pF
Reverse Transfer Capacitance	C_{RSS}		-	25	-	pF

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage	V_{SD}	$I_{SD} = 15\text{A}$	-	-	1.25	V
Reverse Recovery Time	t_{rr}	$I_{SD} = 15\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	45	ns
Reverse Recovered Charge	Q_{RR}	$I_{SD} = 15\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	55	nC

Typical Performance Curves

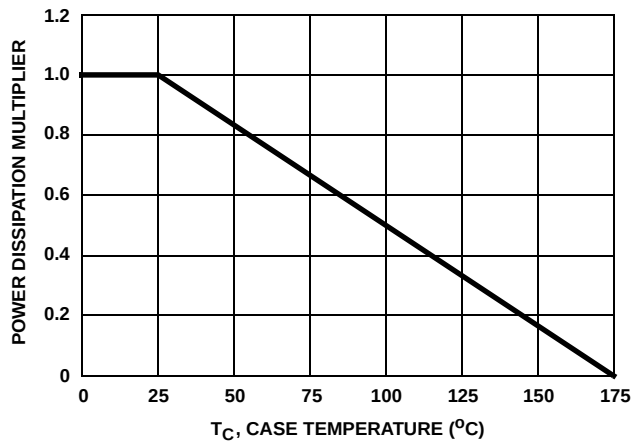


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

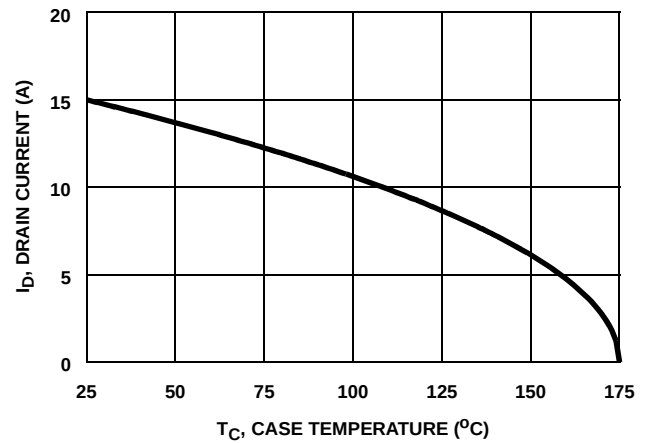


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

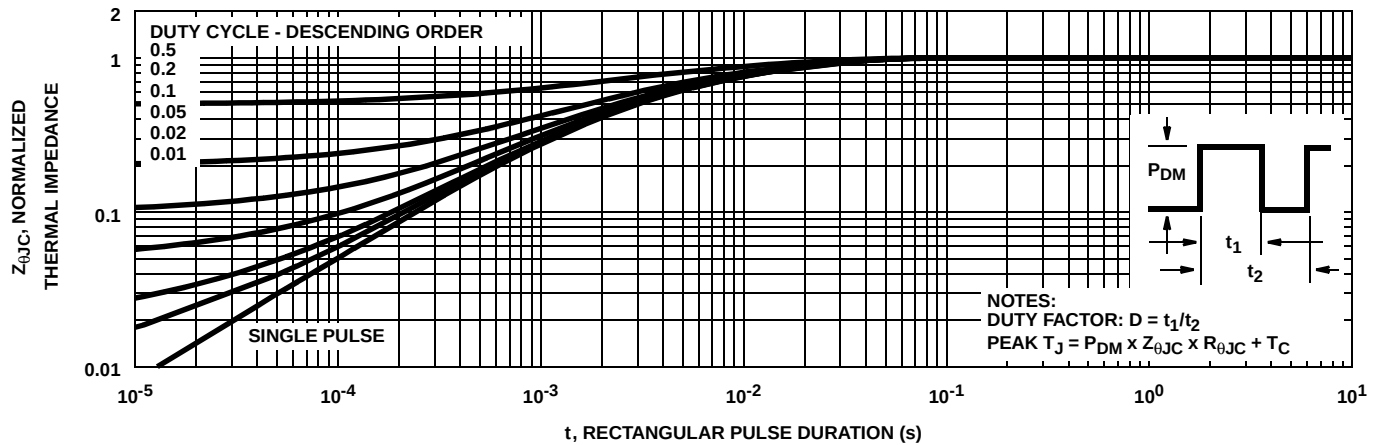


FIGURE 3. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE

Typical Performance Curves (Continued)

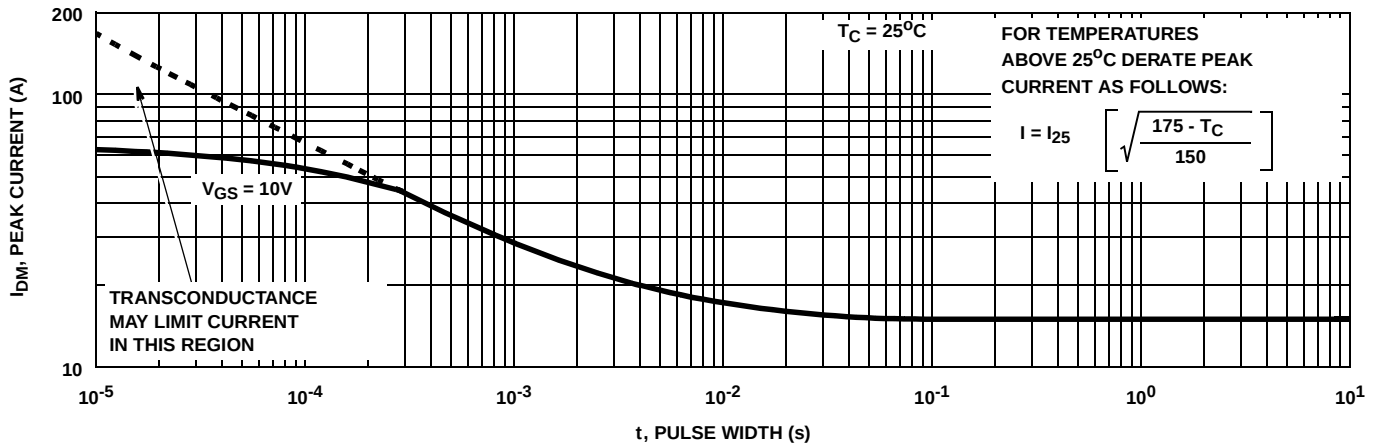


FIGURE 4. PEAK CURRENT CAPABILITY

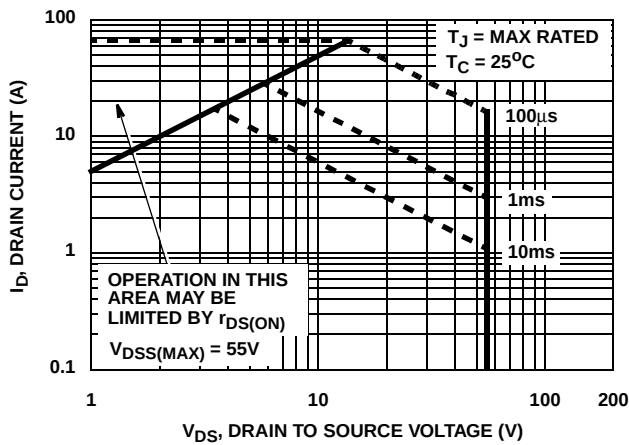
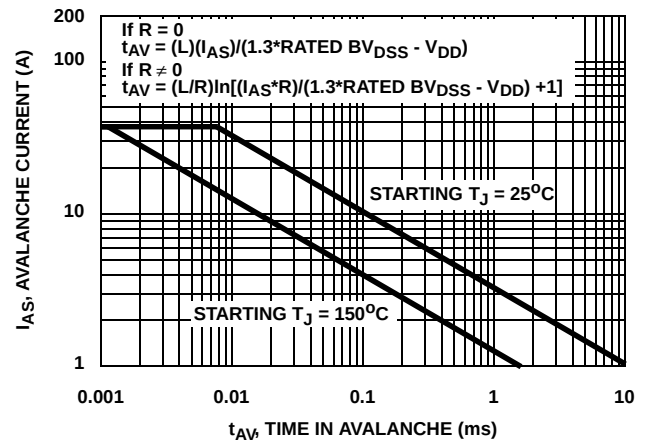


FIGURE 5. FORWARD BIAS SAFE OPERATING AREA



NOTE: Refer to Fairchild Application Notes AN9321 and AN9322.

FIGURE 6. UNCLAMPED INDUCTIVE SWITCHING CAPABILITY

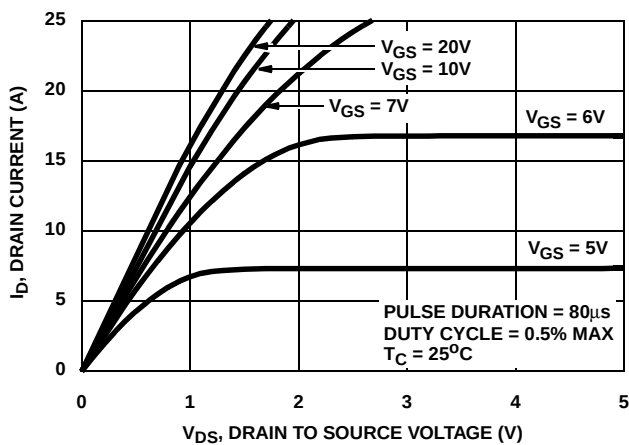


FIGURE 7. SATURATION CHARACTERISTICS

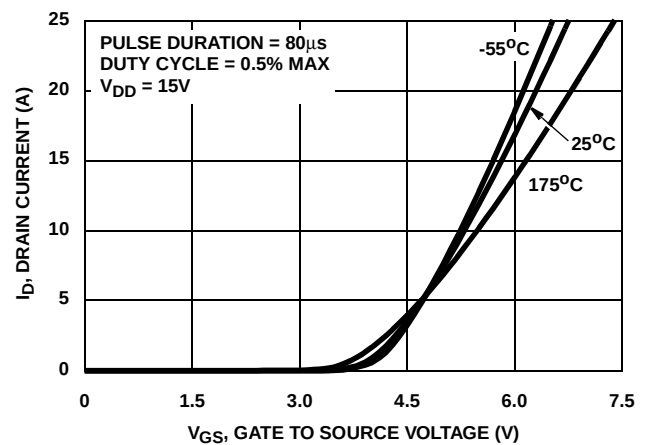


FIGURE 8. TRANSFER CHARACTERISTICS

Typical Performance Curves (Continued)

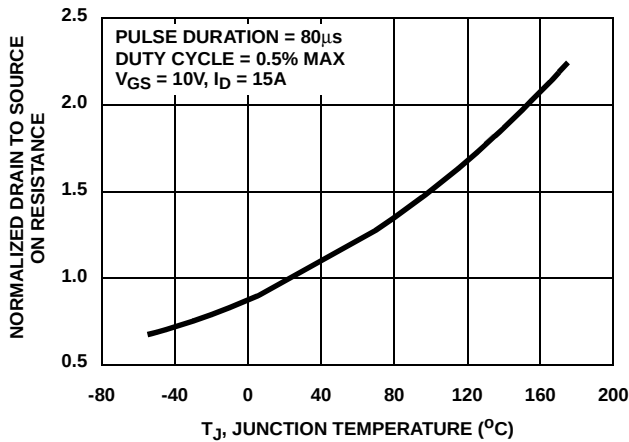


FIGURE 9. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

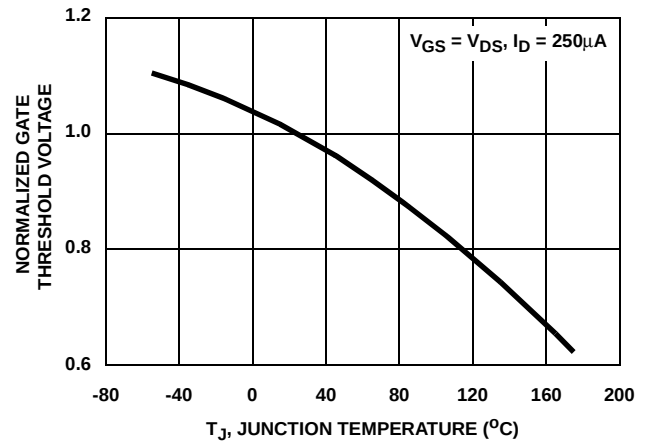


FIGURE 10. NORMALIZED GATE THRESHOLD VOLTAGE vs JUNCTION TEMPERATURE

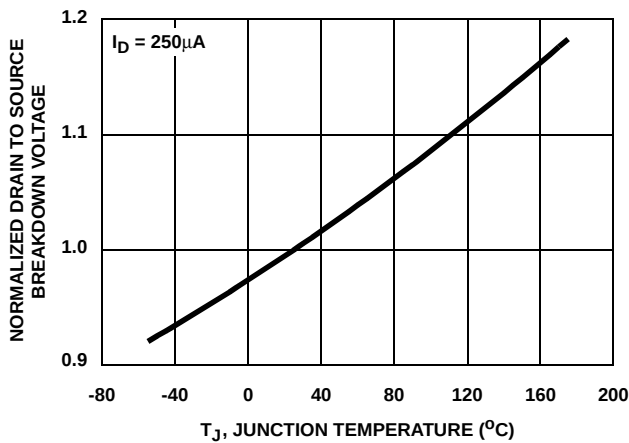


FIGURE 11. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

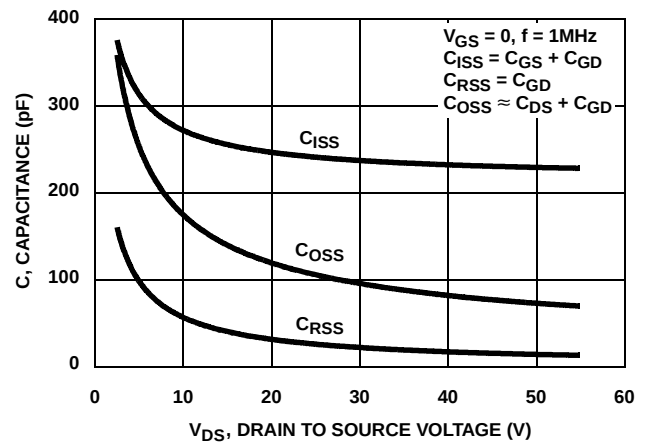
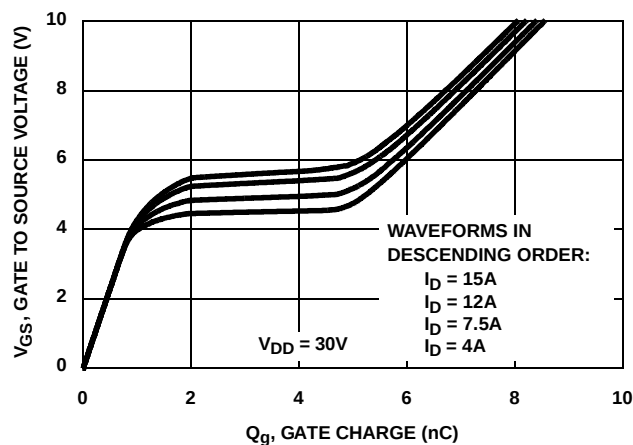


FIGURE 12. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE



NOTE: Refer to Fairchild Application Notes AN7254 and AN7260.

FIGURE 13. GATE CHARGE WAVEFORMS FOR CONSTANT GATE CURRENT

Test Circuits and Waveforms

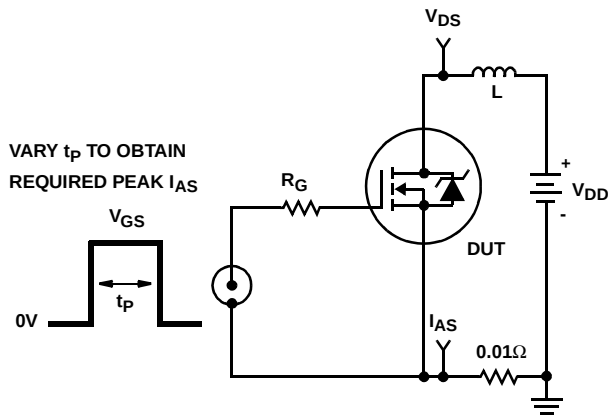


FIGURE 14. UNCLAMPED ENERGY TEST CIRCUIT

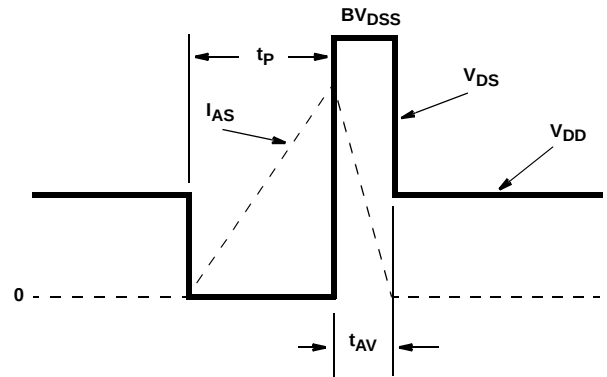


FIGURE 15. UNCLAMPED ENERGY WAVEFORMS

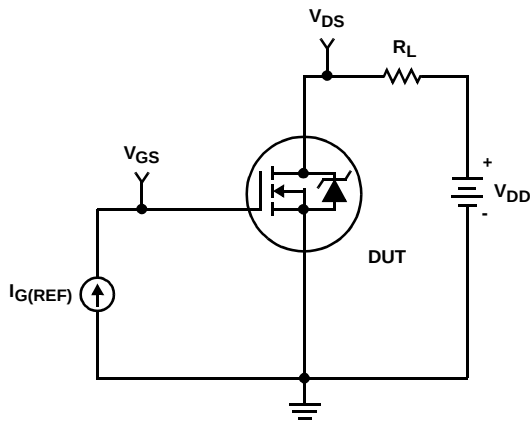


FIGURE 16. GATE CHARGE TEST CIRCUIT

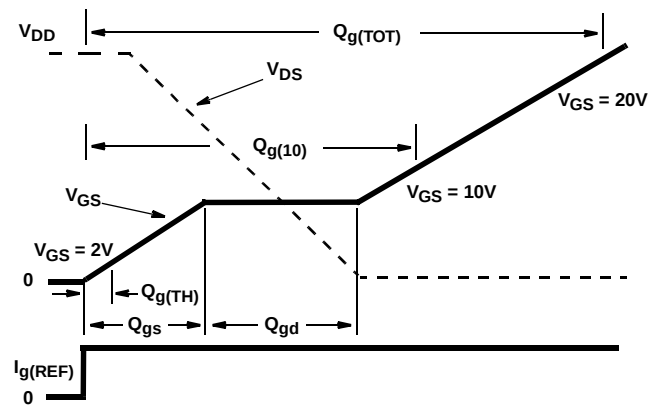


FIGURE 17. GATE CHARGE WAVEFORM

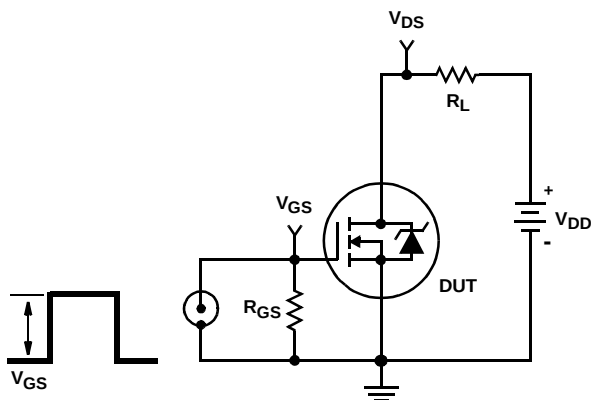


FIGURE 18. SWITCHING TIME TEST CIRCUIT

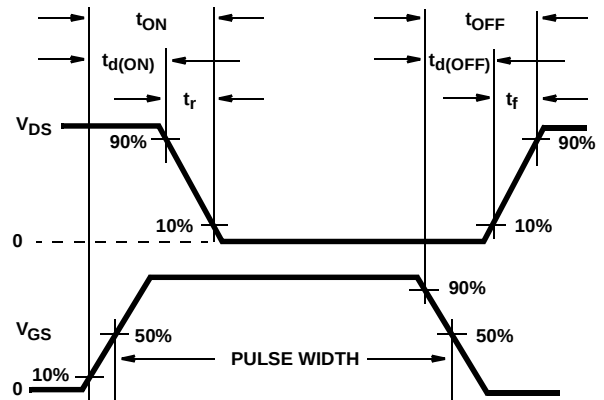


FIGURE 19. RESISTIVE SWITCHING WAVEFORMS

SPICE Thermal Model

REV February 1999

HUF75307

CTHERM1 th 6 8.0e-4
 CHERM2 6 5 1.6e-3
 CHERM3 5 4 1.9e-3
 CHERM4 4 3 2.6e-3
 CHERM5 3 2 5.5e-3
 CHERM6 2 tl 1.8e-2

RHERM1 th 6 8.0e-3
 RHERM2 6 5 2.1e-2
 RHERM3 5 4 2.2e-1
 RHERM4 4 3 6.4e-1
 RHERM5 3 2 7.7e-1
 RHERM6 2 tl 1.0

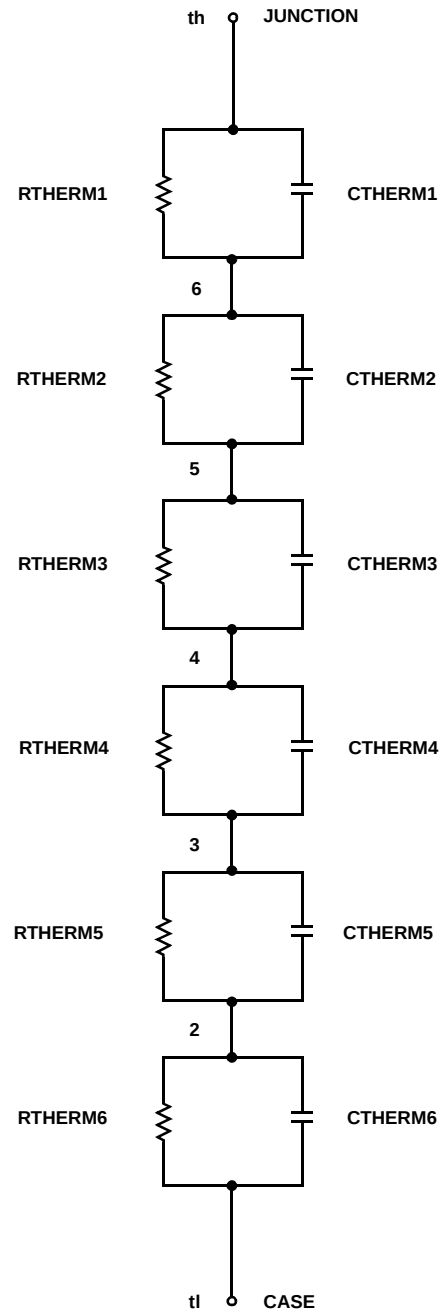
SABER Thermal Model

SABER thermal model HUF75307

template thermal_model th tl
 thermal_c th, tl

```
{
    ctherm.therm1 th 6 = 8.0e-4
    ctherm.therm2 6 5 = 1.6e-3
    ctherm.therm3 5 4 = 1.9e-3
    ctherm.therm4 4 3 = 2.6e-3
    ctherm.therm5 3 2 = 5.5e-3
    ctherm.therm6 2 tl = 1.8e-2
```

```
rtherm.rtherm1 th 6 = 8.0e-3
rtherm.rtherm2 6 5 = 2.1e-2
rtherm.rtherm3 5 4 = 2.2e-1
rtherm.rtherm4 4 3 = 6.4e-1
rtherm.rtherm5 3 2 = 7.7e-1
rtherm.rtherm6 2 tl = 1.0
}
```



TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACE ^{Ex} TM	FAST [®]	OPTOLOGIC TM	SMART START TM	VCX TM
Bottomless TM	FAST ^r TM	OPTOPLANAR TM	STAR*POWER TM	
CoolFET TM	FRFET TM	PACMAN TM	Stealth TM	
CROSSVOLT TM	GlobalOptoisolator TM	POP TM	SuperSOT TM -3	
DenseTrench TM	GTO TM	Power247 TM	SuperSOT TM -6	
DOME TM	HiSeC TM	PowerTrench [®]	SuperSOT TM -8	
EcoSPARK TM	ISOPLANAR TM	QFET TM	SyncFET TM	
E ² CMOS TM	LittleFET TM	QS TM	TinyLogic TM	
EnSigna TM	MicroFET TM	QT Optoelectronics TM	TruTranslation TM	
FACT TM	MicroPak TM	Quiet Series TM	UHC TM	
FACT Quiet Series TM	MICROWIRE TM	SILENT SWITCHER [®]	UltraFET [®]	

STAR*POWER is used under license

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.